



# EMP108

UPDATED 04/04/2008

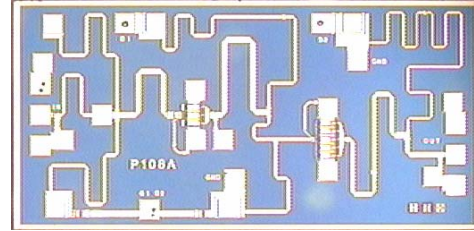
## 7.0 – 9.5 GHz Power Amplifier MMIC

### FEATURES

- 7.0 – 9.5 GHz Operating Frequency Range
- 24.0dBm Output Power at 1dB Compression
- 19.0 dB Typical Small Signal Gain
- -40dBc OIMD3 @Each Tone Pout 14dBm

### APPLICATIONS

- Point-to-point and point-to-multipoint radio
- Military Radar Systems



Dimension: 1130um X 2250um  
Thickness: 75um ± 13um



Caution! ESD sensitive device.

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C, 50 ohm, VDD= 7 V, IDQ= 200 mA)

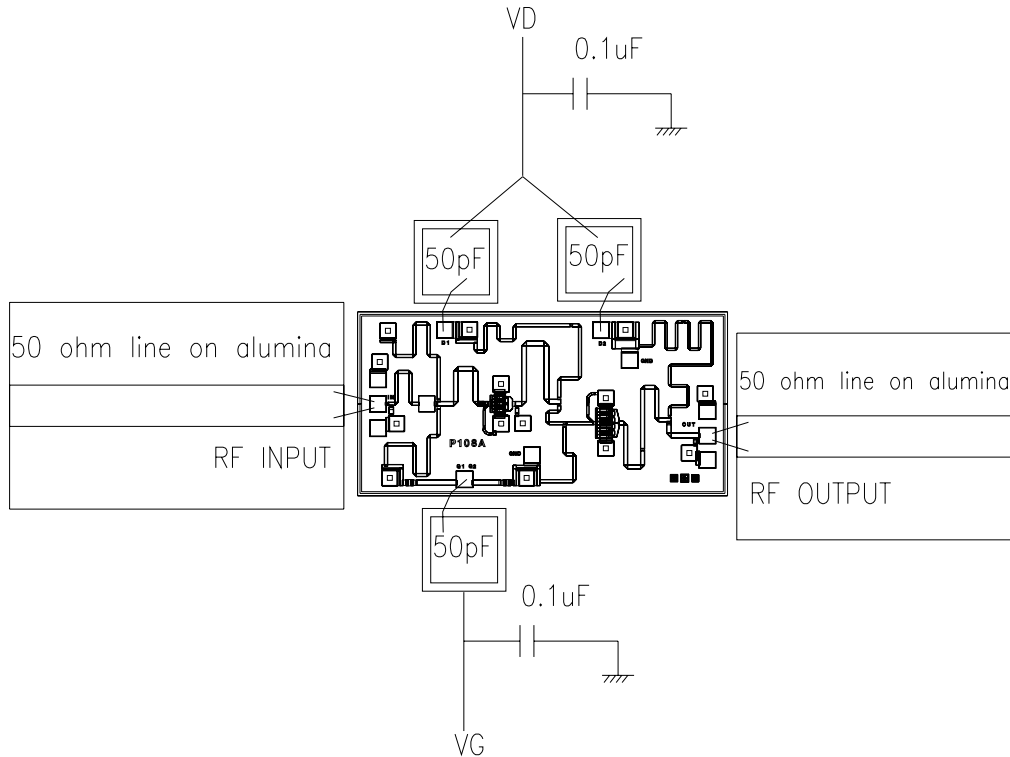
SYMBOL	PARAMETER/TEST CONDITIONS	MIN	TYP	MAX	UNITS
F	Operating Frequency Range	7.0		9.5	GHz
P1dB	Output Power at 1dB Gain Compression	22.5	24.0		dBm
Gss	Small Signal Gain	16.0	19.0		dB
OIMD3	Output 3 <sup>rd</sup> Order Intermodulation Distortion @Δf=10MHz, Each Tone Pout 14dBm		-40	-38	dBc
Input RL	Input Return Loss		-10		dB
Output RL	Output Return Loss		-5		dB
Idss	Saturate Drain Current V <sub>DS</sub> =3V, V <sub>GS</sub> =0V	225	305	366	mA
VDD	Power Supply Voltage	7		8	V
Rth	Thermal Resistance (Au-Sn Eutectic Attach)		30		°C/W
Tb	Operating Base Plate Temperature	- 35		+ 85	°C

### ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION<sup>1,2</sup>

SYMBOL	CHARACTERISTIC	VALUE
V <sub>DS</sub>	Drain to Source Voltage	8 V
V <sub>GS</sub>	Gate to Source Voltage	- 4 V
I <sub>DD</sub>	Drain Current	Idss
I <sub>GSF</sub>	Forward Gate Current	4.5 mA
P <sub>IN</sub>	Input Power	@ 3dB compression
T <sub>CH</sub>	Channel Temperature	150°C
T <sub>STG</sub>	Storage Temperature	-65/150°C
P <sub>T</sub>	Total Power Dissipation	3.8W

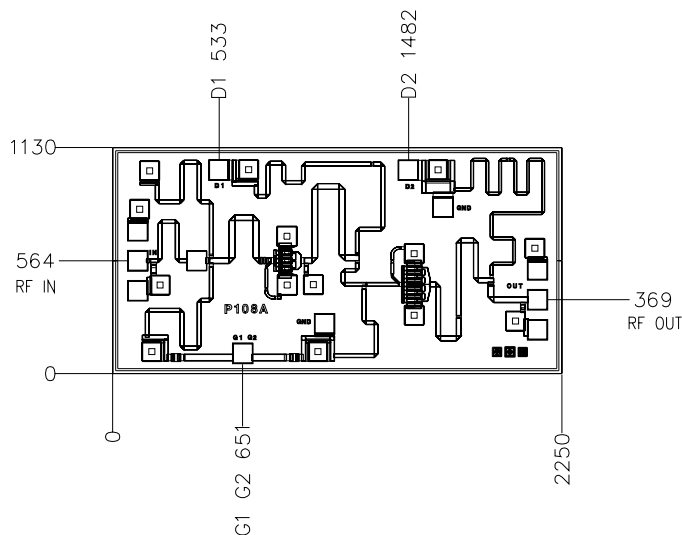
1. Operating the device beyond any of the above rating may result in permanent damage.
2. Bias conditions must also satisfy the following equation  $V_{DS} * I_{DS} < (T_{CH} - T_{HS}) / R_{TH}$ ; where T<sub>HS</sub> = ambient temperature

### ASSEMBLY DRAWING



The length of RF wires should be as short as possible. Use at least two wires between RF pad and 50 ohm line and separate the wires to minimize the mutual inductance.

### CHIP OUTLINE



Chip Size 1130 x 2250 microns  
 Chip Thickness: 75 ± 13 microns  
 PAD Dimensions: 100 x 100 microns  
 All Dimensions in Microns

Specifications are subject to change without notice.

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page 2 of 2  
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